

GaAs MMIC SMT PASSIVE FREQUENCY DOUBLER, 2 - 4 GHz INPUT

Typical Applications

The HMC189MS8 is suitable for:

- Wireless Local Loop
- LMDS, VSAT, and Pt to Pt Radios
- UNII & HiperLAN
- Test Equipment

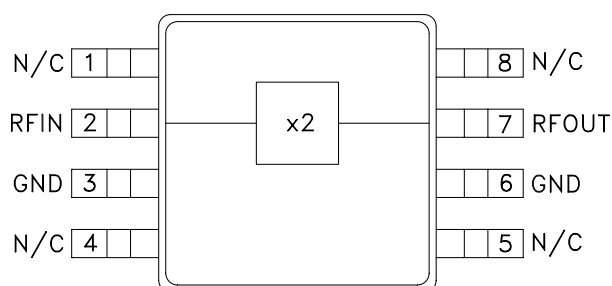
Features

Conversion Loss: 13 dB

Fo, 3Fo, 4Fo Isolation: 33 dB

Input Drive Level: +10 to +15 dBm

Functional Diagram



General Description

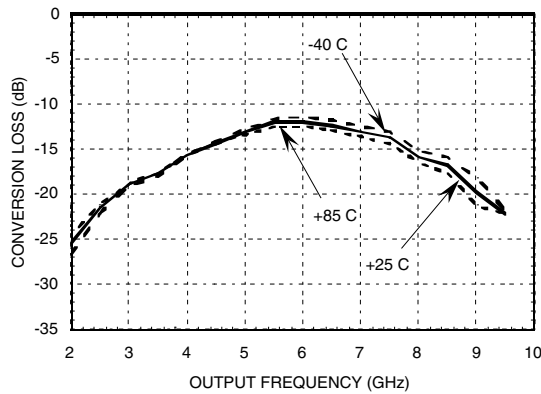
The HMC189MS8 is a miniature passive frequency doubler in a plastic 8-lead MSOP package. The suppression of undesired fundamental and higher order harmonics is 33 dB typical with respect to input signal levels. The doubler uses the same diode/balun technology used in Hittite MMIC mixers. The doubler is ideal for high volume applications where frequency doubling of a lower frequency is more economical than directly generating a higher frequency. The passive Schottky diode doubler technology contributes no measurable additive phase noise onto the multiplied signal.

Electrical Specifications, $T_A = +25^\circ\text{C}$, As a Function of Drive Level

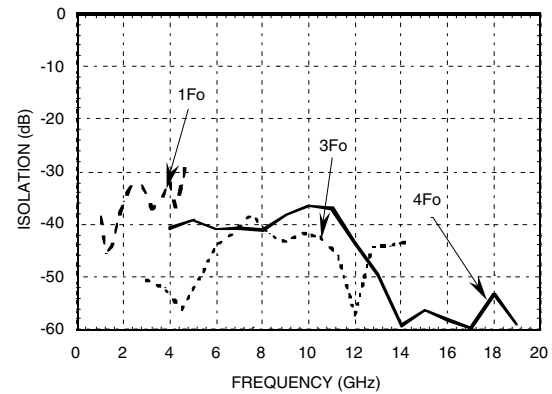
Parameter	Input = +10 dBm			Input = +13 dBm			Input = +15 dBm			Units
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
Frequency Range, Input	2.5 - 3.5			2.5 - 3.75			2 - 4			GHz
Frequency Range, Output	5 - 7			5 - 7.5			4 - 8			GHz
Conversion Loss		13	17		13	15		13	17	dB
FO Isolation (with respect to input level)	29	32		30	33		31	34		dB
3FO Isolation (with respect to input level)	37	43		35	42		33	40		dB
4FO Isolation (with respect to input level)	32	40		33	40		31	40		dB

GaAs MMIC SMT FREQUENCY DOUBLER, 2 - 4 GHz INPUT

Conversion Loss @ +13 dBm Drive Level

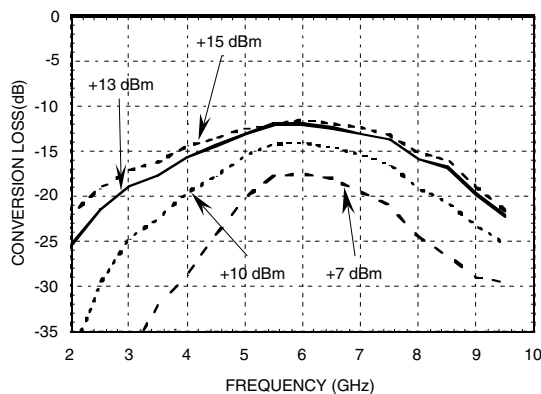


Isolation* @ +13 dBm Drive Level

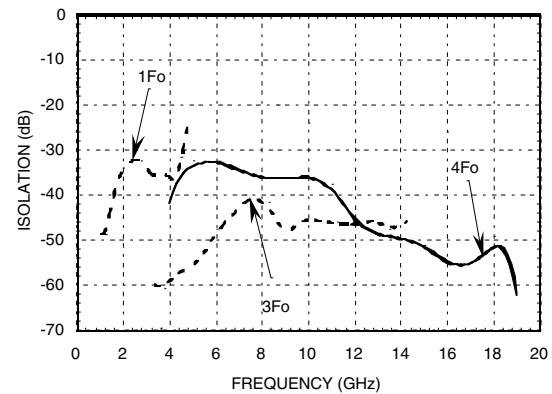


* With respect to input level

Conversion Loss vs. Drive Level

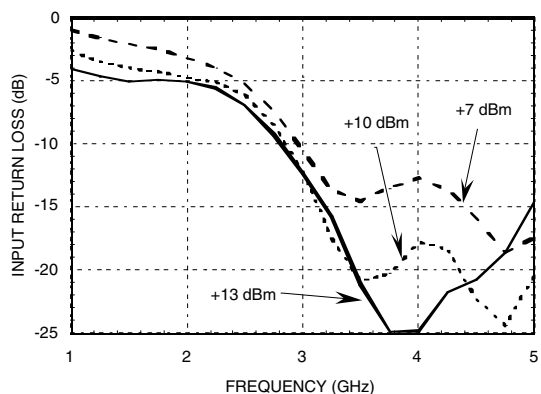


Isolation* @ +10 dBm Drive Level

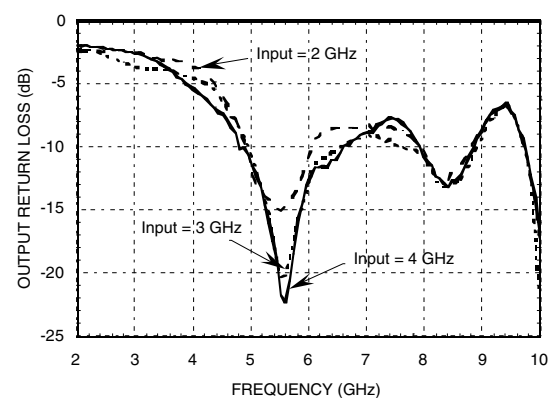


* With respect to input level

Input Return Loss vs. Drive Level



Output Return Loss for Several Input Frequencies

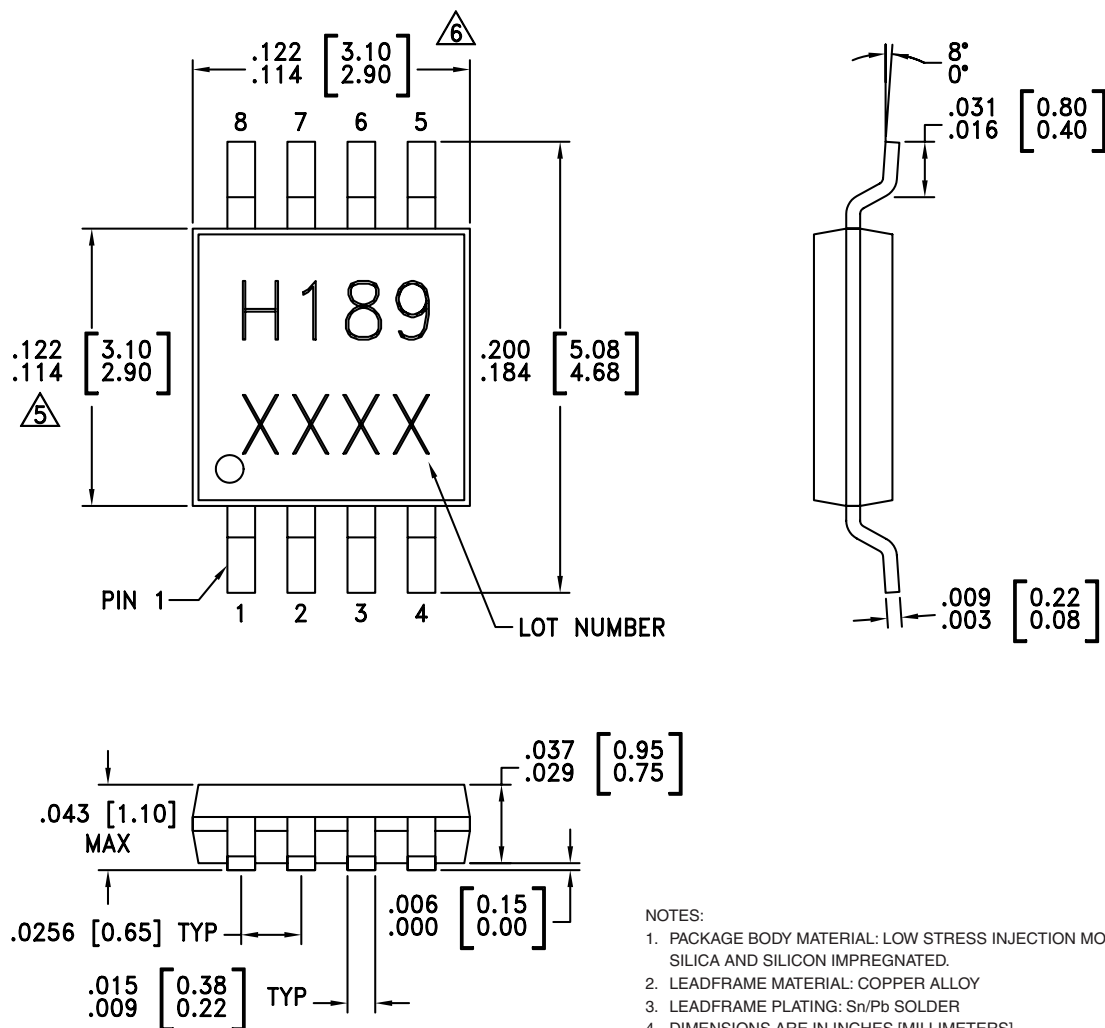


GaAs MMIC SMT FREQUENCY DOUBLER, 2.0 - 4.0 GHz INPUT

Absolute Maximum Ratings

Input Drive	+27 dBm
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C

Outline Drawing

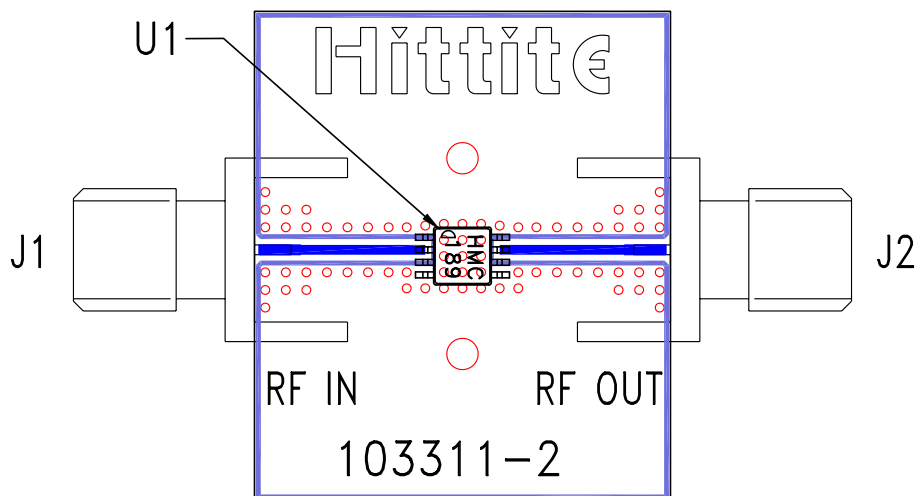


NOTES:

1. PACKAGE BODY MATERIAL: LOW STRESS INJECTION MOLDED PLASTIC SILICA AND SILICON IMPREGNATED.
2. LEADFRAME MATERIAL: COPPER ALLOY
3. LEADFRAME PLATING: Sn/Pb SOLDER
4. DIMENSIONS ARE IN INCHES [MILLIMETERS].
5. DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15 mm PER SIDE.
6. DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25 mm PER SIDE.
7. ALL GROUND LEADS MUST BE SOLDERED TO PCB PF GROUND.

GaAs MMIC SMT FREQUENCY DOUBLER, 2.0 - 4.0 GHz INPUT

Evaluation PCB



The circuit board used in the final application should be generated with proper RF circuit design techniques. Signal lines at the RF port should have 50 ohm impedance and the package ground leads should be connected directly to the ground plane similar to that shown above. The evaluation circuit board shown above is available from Hittite Microwave Corporation upon request.

List of Materials

Item	Description
J1, J2	PC Mount SMA Connector
U1	HMC189MS8 Doubler
PCB*	103311 Eval Board
*Circuit Board Material: Rogers 4350	